

SPB18P06PG-VB Datasheet

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ)
- 60	0.064 at $V_{GS} = - 10$ V	- 30	12
	0.077 at $V_{GS} = - 4.5$ V	- 28	

FEATURES

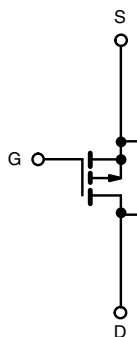
- Trench Power MOSFET 100
- % UIS Tested

APPLICATIONS

- Load Switch



RoHS
COMPLIANT
HALOGEN
FREE



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175\text{ }^\circ\text{C}$)	$T_C = 25\text{ }^\circ\text{C}$	I_D	- 30	A
	$T_C = 100\text{ }^\circ\text{C}$		- 20	
Pulsed Drain Current		I_{DM}	- 90	
Continuing Source Current (Diode Conduction)		I_S	- 28	
Avalanche Current		I_{AS}	- 31	
Single Pulse Avalanche Energy	$L = 0.1\text{ mH}$	E_{AS}	7.2	mJ
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	60 ^a	W
	$T_A = 25\text{ }^\circ\text{C}$		6 ^b	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^b	$t \leq 10\text{ sec}$	R_{thJA}	20	25	$^\circ\text{C/W}$
	Steady State		62	75	
Junction-to-Case		R_{thJC}	5	6	

Notes:

a. See SOA curve for voltage derating.

b. Surface Mounted on 1" x 1" FR-4 board.

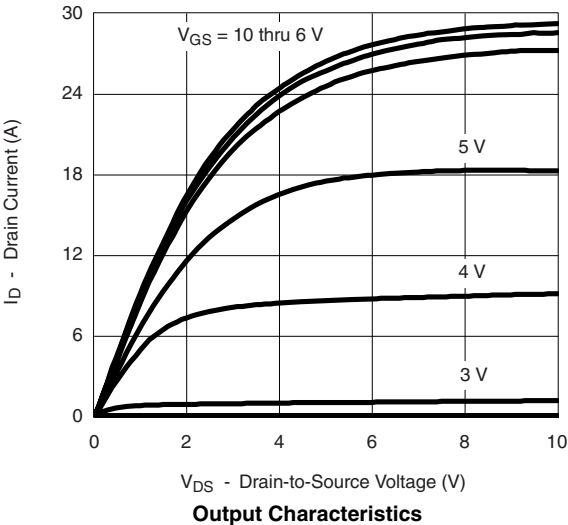
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1.0	- 2.0	- 3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 175 °C			- 150	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 10			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = - 10 V, I _D = - 5 A		0.064		Ω
		V _{GS} = - 10 V, I _D = - 5 A, T _J = 125 °C		0.110		
		V _{GS} = - 10 V, I _D = - 5 A, T _J = 175 °C		0.250		
		V _{GS} = - 4.5 V, I _D = - 2 A		0.077		
Forward Transconductance ^b	g _{fs}	V _{DS} = - 15 V, I _D = - 5 A		8		S
Dynamic						
Input Capacitance	C _{iss}	V _{DS} = - 25 V, V _{GS} = 0 V, f = 1 MHz		1000		pF
Output Capacitance	C _{oss}			210		
Reverse Transfer Capacitance	C _{rss}			110		
Total Gate Charge	Q _g	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 8.4 A		12.5	19	nC
Gate-Source Charge	Q _{gs}			2.3		
Gate-Drain Charge	Q _{gd}			3.2		
Gate Resistance	R _g	f = 1 MHz		8.0		Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 30 V, R _L = 3.57 Ω I _D ≅ - 8.4 A, V _{GEN} = - 10 V, R _G = 2.5 Ω		5	10	ns
Rise Time ^c	t _r			14	25	
Turn-Off Delay Time ^c	t _{d(off)}			15	25	
Fall Time ^c	t _f			7	12	
Source-Drain Diode Ratings and Characteristics (T _C = 25 °C) ^b						
Pulsed Current	I _{SM}				- 30	A
Forward Voltage ^b	V _{SD}	I _F = - 2 A, V _{GS} = 0 V		- 0.9	- 1.3	V
Reverse Recovery Time	t _{rr}	I _F = - 8 A, di/dt = 100 A/μs		50	80	ns
Reverse Recovery Time	Q _{rr}			80	120	nC

Notes:

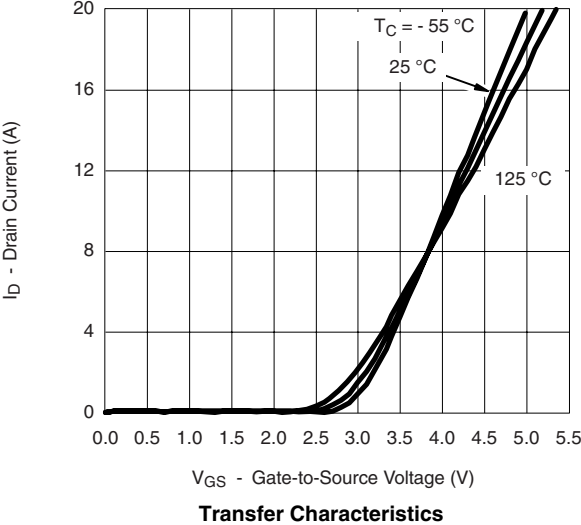
- a. Guaranteed by design, not subject to production testing.
 b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

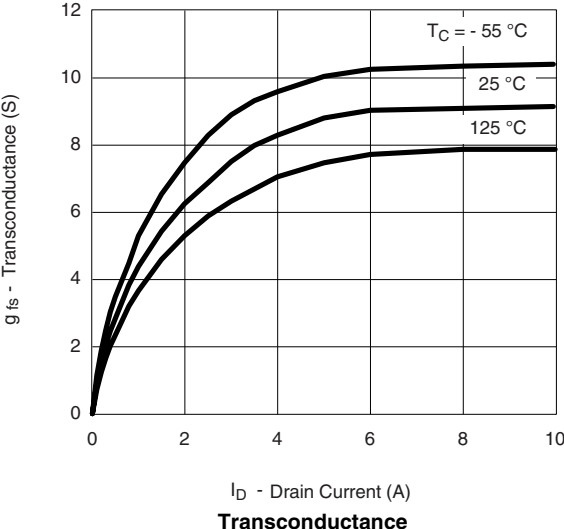
TYPICAL CHARACTERISTICS 25 °C unless noted



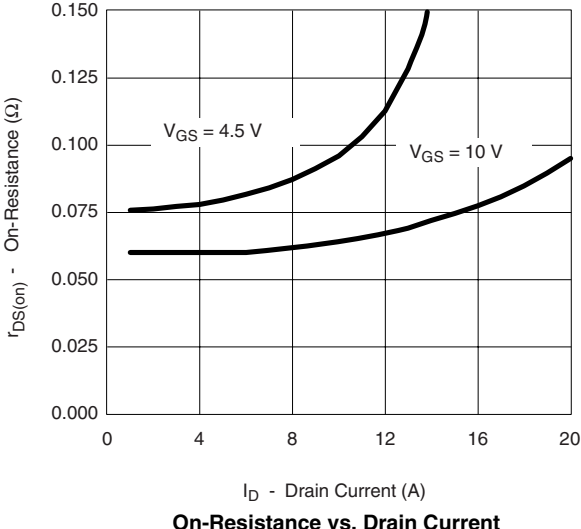
Output Characteristics



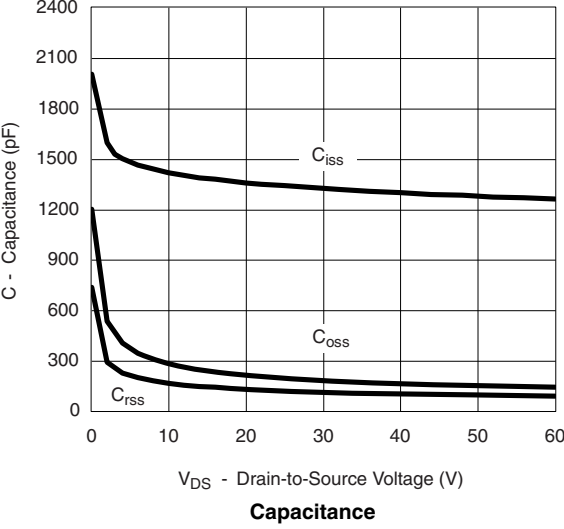
Transfer Characteristics



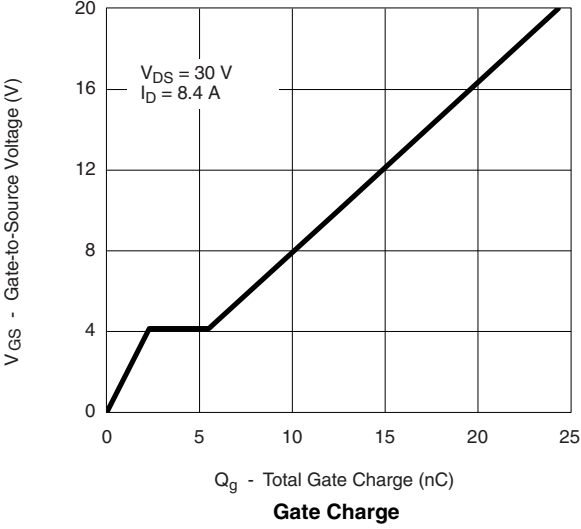
Transconductance



On-Resistance vs. Drain Current

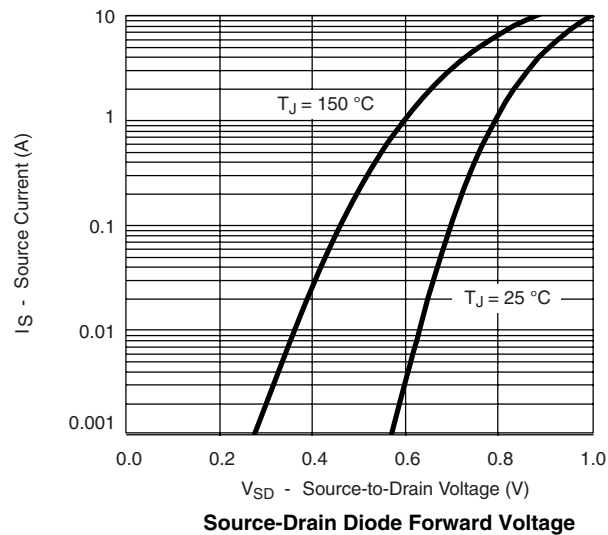
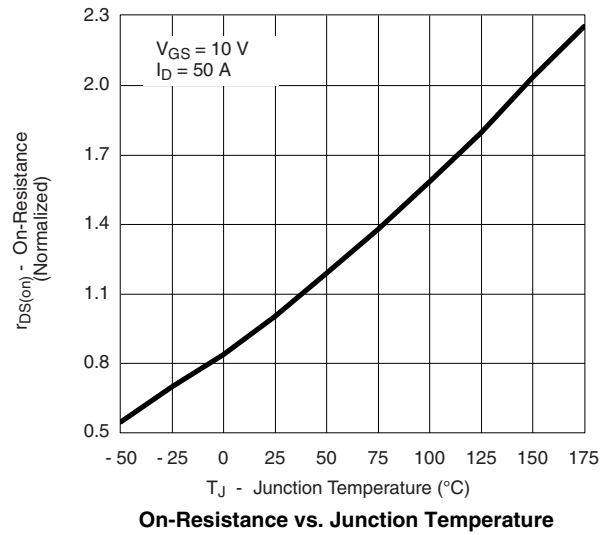


Capacitance

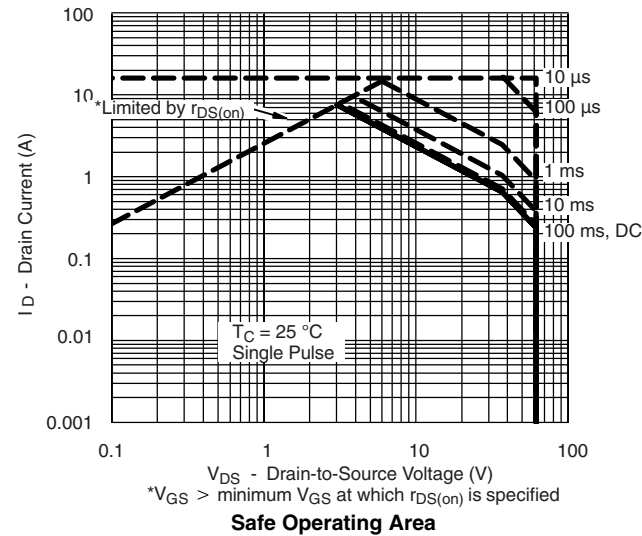
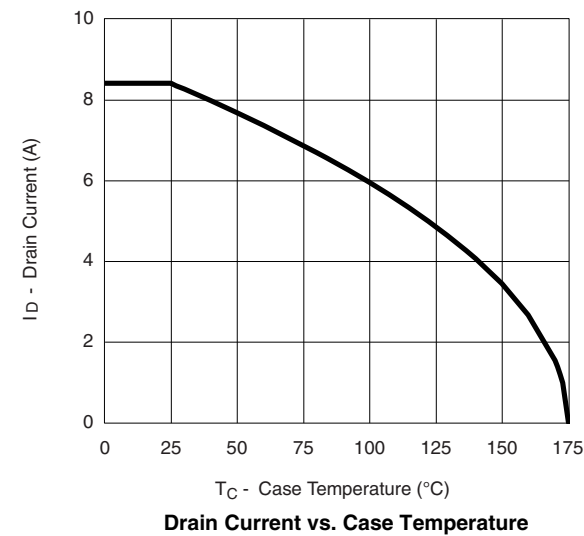


Gate Charge

TYPICAL CHARACTERISTICS 25 °C unless noted



THERMAL RATINGS



THERMAL RATINGS**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

Technical drawing of a mechanical part, likely a lead tip or probe, showing multiple views and annotations.

Views:

- Top View:** Shows dimensions $L1$, D , H , E , and $L2$. It includes feature control frames for circular runout ($\phi 0.010 \text{ M AM B}$) and surface texture ($\text{R} \pm 0.004 \text{ M B}$). Datum A is indicated.
- Front View:** Shows dimensions A , $c2$, and c . It includes a detail view of the lead tip.
- Section B-B and C-C:** Shows cross-sections with dimensions $b1$, $b3$, $c1$, c , and $(b, b2)$. It identifies "Plating" and "Base metal".
- Detail A:** A magnified view of the lead tip, showing dimensions $L3$, $L4$, and $A1$. It includes a gauge plane and a seating plane.
- View A-A:** A cross-section view showing dimensions E , $D1$, and $E1$.

Annotations:

- Datum A:** Indicated by a triangle and the letter A.
- Feature Control Frames:**
 - $\phi 0.010 \text{ M AM B}$ (Circular runout)
 - $\text{R} \pm 0.004 \text{ M B}$ (Surface texture)
- Section Labels:** "Section B - B and C - C", "Scale: none".
- Detail Labels:** "Detail A", "Detail 'A' Rotated 90° CW scale 8:1".
- View Labels:** "View A - A".
- Other Labels:** "Lead tip", "Gauge plane", "Seating plane", "Plating", "Base metal".

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead

Recommended Minimum Pads
Dimensions in Inches/(mm)

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